

150 V, 500 mA NPN high-voltage low VCEsat (BISS) transistor19 November 2015Product data sheet

1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBHV9515QA.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\rm I}_{\rm C}$ and ${\rm I}_{\rm CM}$
- High collector current gain (h_{FE}) at high I_C
- Low package height of 0.37 mm
- AEC-Q101 qualified
- Suitable for Automatic Optical Inspection (AOI) of solder joint

3. Applications

- LED driver for LED chain module
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. C	uick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	150	V
I _C	collector current		-	-	500	mA
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; \text{ I}_{C} = 100 \text{ mA}; \text{ pulsed};$ $t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C}$	100	215	-	

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	E	emitter		в
3	С	collector	4 3	► T
4	С	collector	Transparent top view DFN1010D-3 (SOT1215)	E sym123

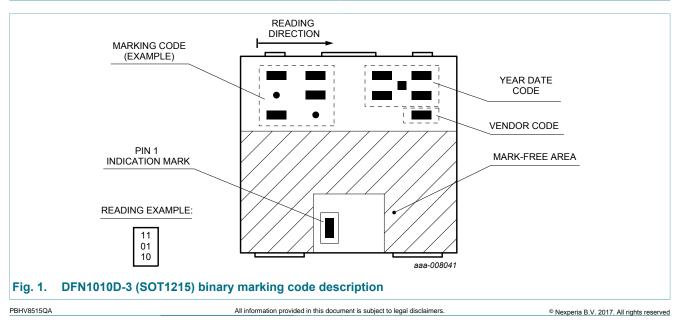
6. Ordering information

Table 3. Ordering in	formation				
Type number	Package				
	Name	Description	Version		
PBHV8515QA	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV8515QA	00 00 11



8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	150	V
V _{CEO}	collector-emitter voltage	open base		-	150	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	500	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	1	А
I _{BM}	peak base current	_		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

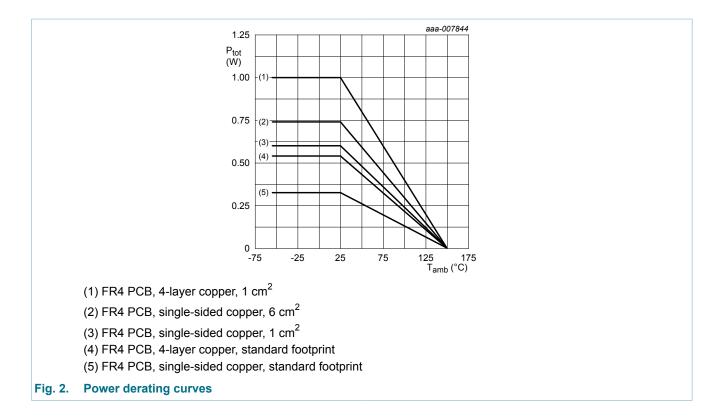
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

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9. Thermal characteristics

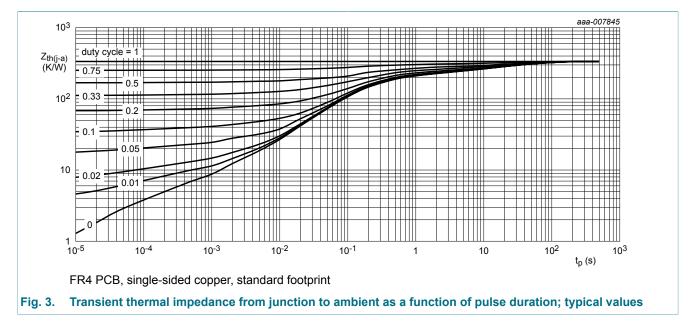
Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	385	K/W
			[2]	-	-	209	K/W
	ampient		[3]	-	-	169	K/W
		[4]	-	-	232	K/W	
		[5]	-	-	125	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

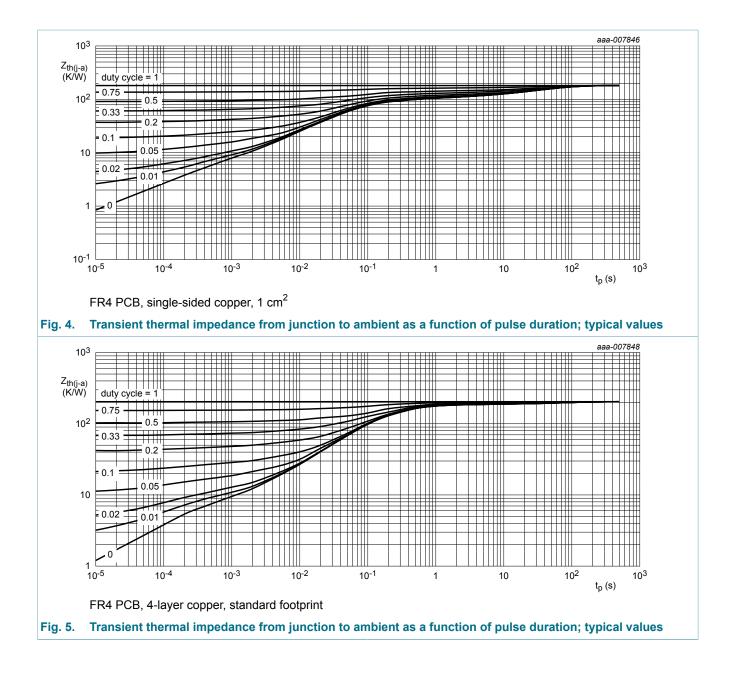
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



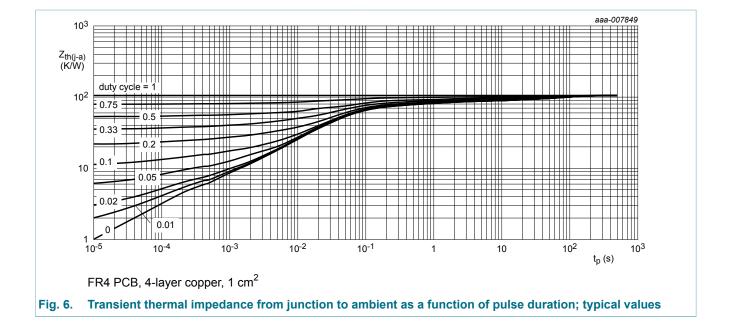
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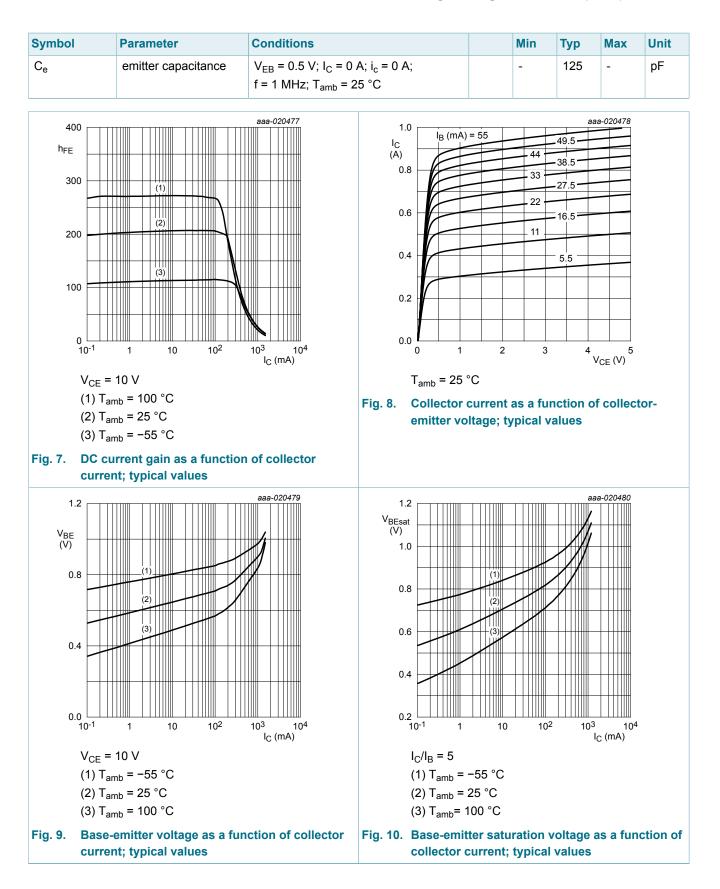


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 120 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 120 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I _C = 50 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	100	215	-	
		V_{CE} = 10 V; I _C = 100 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	100	215	-	
		V_{CE} = 10 V; I _C = 200 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	100	200	-	
		$V_{CE} = 10 \text{ V}; \text{ I}_{C} = 500 \text{ mA}; \text{ pulsed};$ $t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02; \text{T}_{amb} = 25 ^{\circ}\text{C}$	35	60	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 50 mA; I_{B} = 5 mA; T_{amb} = 25 °C	-	30	60	mV
		$\begin{split} & \textbf{I}_{C} = 100 \text{ mA}; \text{ I}_{B} = 10 \text{ mA}; \text{ pulsed}; \\ & \textbf{t}_{p} \leq 300 \mu\text{s}; \delta \leq 0.02; \textbf{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	45	80	mV
		I_{C} = 100 mA; I_{B} = 20 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; T_{amb} = 25 °C	-	35	70	mV
		I_{C} = 200 mA; I_{B} = 40 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; T_{amb} = 25 °C	-	60	100	mV
		I_C = 500 mA; I_B = 100 mA; pulsed;	-	120	200	mV
V _{BEsat}	base-emitter saturation voltage	$t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^\circ C$	-	0.95	1.2	V
t _d	delay time	V_{CC} = 10 V; I _C = 100 mA; I _{Bon} = 20 mA;	-	15	-	ns
r	rise time	I_{Boff} = -20 mA; T_{amb} = 25 °C	-	155	-	ns
ton	turn-on time		-	170	-	ns
s	storage time		-	650	-	ns
f	fall time		-	170	-	ns
off	turn-off time		-	820	-	ns
fT	transition frequency	V_{CE} = 10 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C	-	75	-	MHz
C _c	collector capacitance	V _{CB} = 20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	2.4	-	pF

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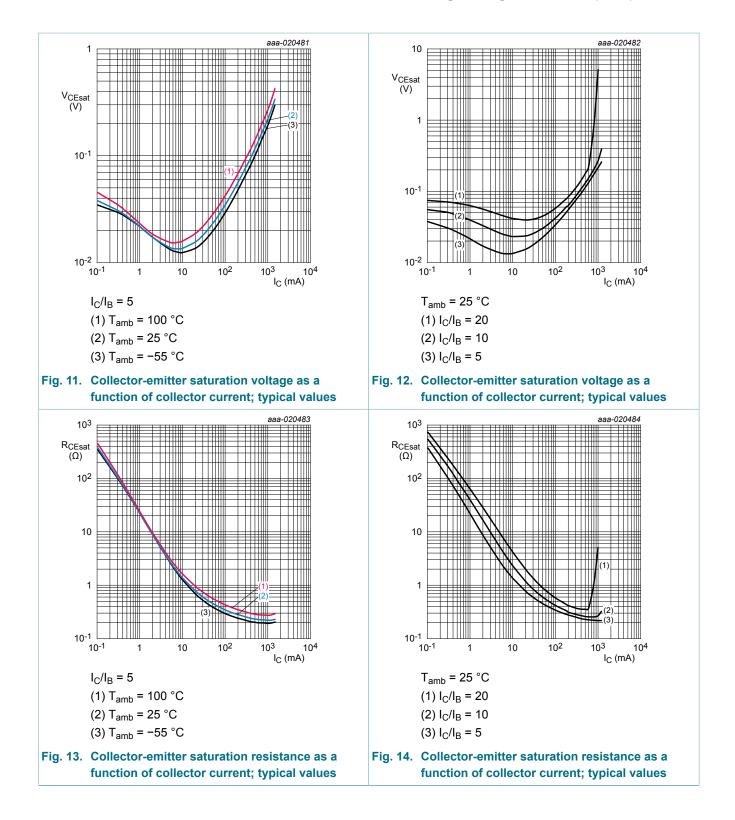


PBHV8515QA Product data sheet

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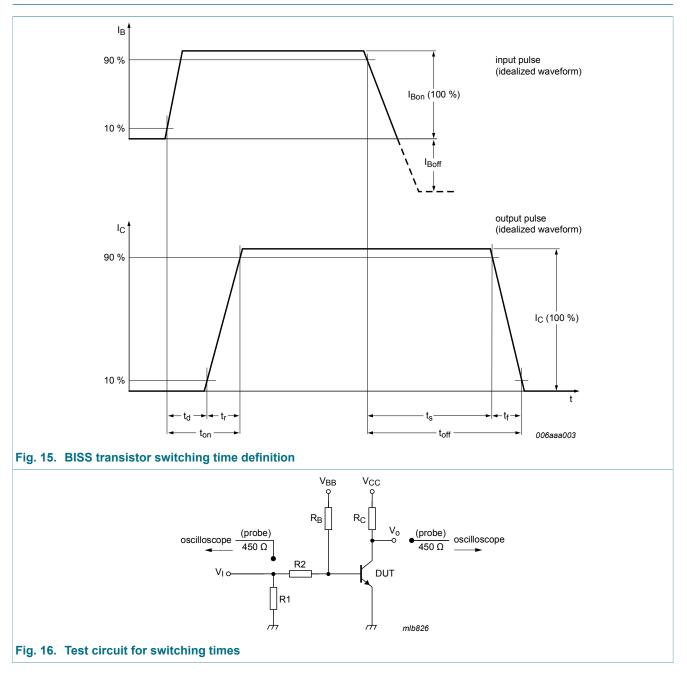
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11. Test information

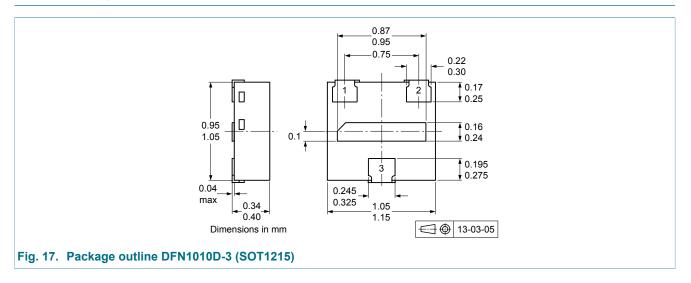


11.1 Quality information

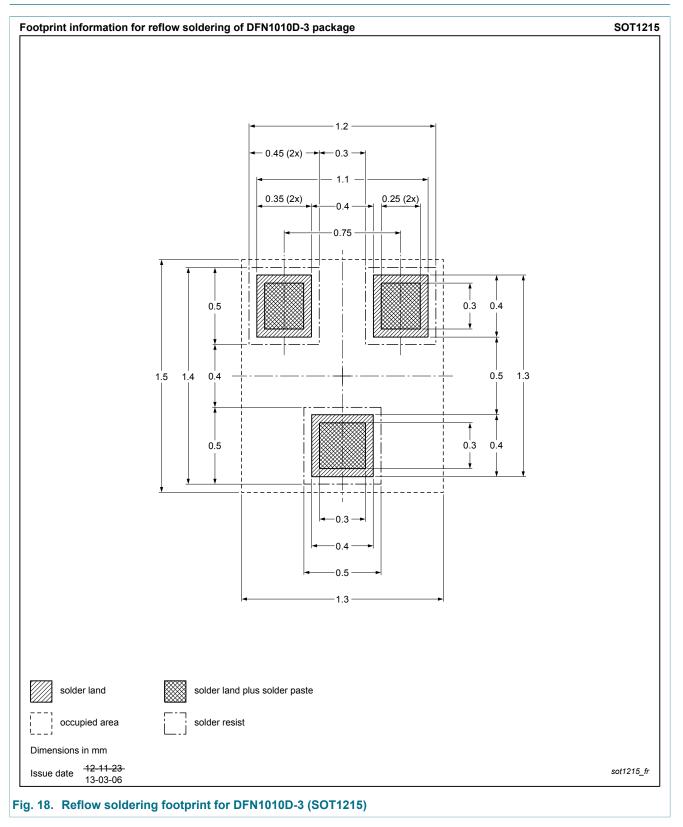
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

PBHV8515QA

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBHV8515QA v.1	20151119	Product data sheet	-	-				

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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